Pb Free Terminal Finish.

ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

PRODUCT APPLICATIONS

- Anti-Parallel Diode

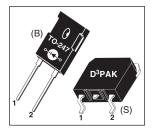
 Switchmode Power Supply
 Inverters
- Free Wheeling Diode
 - -Motor Controllers
 - -Converters
 - -Inverters
- Snubber Diode
- PFC

PRODUCT FEATURES

- Ultrafast Recovery Times
- Soft Recovery Characteristics
- Popular TO-247 Package or Surface Mount D³PAK Package
- Low Forward Voltage
- Low Leakage Current
- Avalanche Energy Rated

PRODUCT BENEFITS

- Low Losses
- · Low Noise Switching
- Cooler Operation
- . Higher Reliability Systems
- Increased System Power Density





- 1 Cathode
- 2 Anode Back of Case - Cathode

MAXIMUM RATINGS

All Ratings: $T_C = 25^{\circ}C$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT15DQ60(B/S)G	UNIT	
V _R	Maximum D.C. Reverse Voltage			
V _{RRM}	Maximum Peak Repetitive Reverse Voltage	600	Volts	
V _{RWM}	Maximum Working Peak Reverse Voltage			
I _{F(AV)}	Maximum Average Forward Current (T _C = 129°C, Duty Cycle = 0.5)	15		
I _{F(RMS)}	RMS Forward Current (Square wave, 50% duty)	30	Amps	
I _{FSM}	Non-Repetitive Forward Surge Current (T _J = 45°C, 8.3ms)	110		
E _{AVL}	Avalanche Energy (1A, 40mH)	20	mJ	
T _J ,T _{STG}	Operating and StorageTemperature Range	-55 to 175	ာ့ သ	
T _L	Lead Temperature for 10 Sec.	300		

STATIC ELECTRICAL CHARACTERISTICS

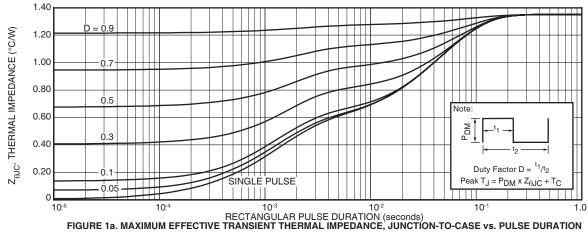
Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
V _F	Forward Voltage	I _F = 15A		2.0	2.4	Volts
		I _F = 30A		2.5		
		I _F = 15A, T _J = 125°C		1.56		
I _{RM}	Maximum Reverse Leakage Current	V _R = 600V			25	μA
		$V_{R} = 600V, T_{J} = 125^{\circ}C$			500	
C _T	Junction Capacitance, V _R = 200V			25		pF

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t _{rr}	Reverse Recovery Time I _F = 1A, di _F /dt =	$-100A/\mu s$, $V_R = 30V$, $T_J = 25$ °C	-	15		nc
t _{rr}	Reverse Recovery Time	$I_F = 15A$, $di_F/dt = -200A/\mu s$ $V_R = 400V$, $T_C = 25^{\circ}C$	-	19		ns
Q _{rr}	Reverse Recovery Charge		-	21		nC
I _{RRM}	Maximum Reverse Recovery Current		-	2	-	Amps
t _{rr}	Reverse Recovery Time	$I_F = 15A$, $di_F/dt = -200A/\mu s$ $V_R = 400V$, $T_C = 125^{\circ}C$	-	105		ns
Q _{rr}	Reverse Recovery Charge		-	250		nC
I _{RRM}	Maximum Reverse Recovery Current		-	5	-	Amps
t _{rr}	Reverse Recovery Time	$I_F = 15A$, $di_F/dt = -1000A/\mu s$ $V_R = 400V$, $T_C = 125°C$	-	55		ns
Q _{rr}	Reverse Recovery Charge		-	420		nC
I _{RRM}	Maximum Reverse Recovery Current		-	15		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			1.35	°C/W
W _T	Package Weight		0.22		oz
			5.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

Microsemi reserves the right to change, without notice, the specifications and information contained herein.



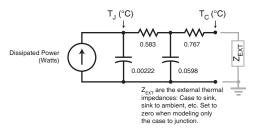
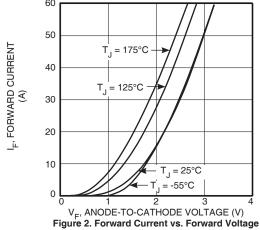


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

TYPICAL PERFORMANCE CURVES



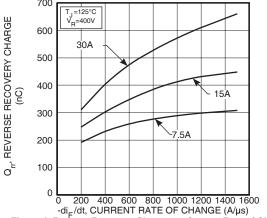
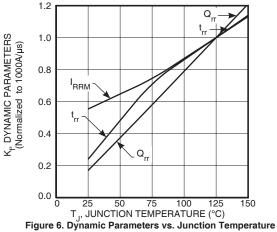
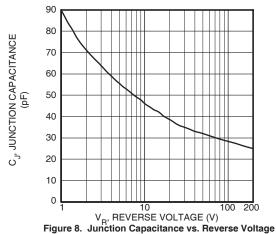


Figure 4. Reverse Recovery Charge vs. Current Rate of Change





APT15DQ60(B/S)G

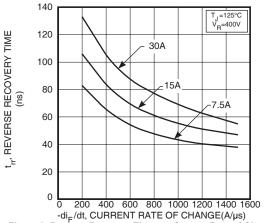
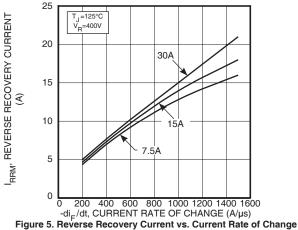


Figure 3. Reverse Recovery Time vs. Current Rate of Change



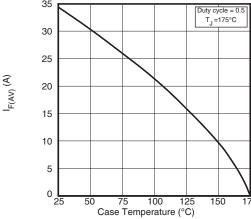


Figure 7. Maximum Average Forward Current vs. CaseTemperature

Figure 9. Diode Test Circuit

- 1 I_F Forward Conduction Current
- 2 di_F/dt Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} Maximum Reverse Recovery Current.
- 4 t_{rr} Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and 0.25•I_{RRM} passes through zero.
- 5 Q_{rr} Area Under the Curve Defined by I_{RRM} and t_{rr}.

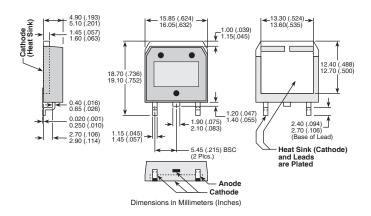
Figure 10, Diode Reverse Recovery Waveform and Definitions

TO-247 Package Outline

4.69 (185) 5.31 (209) 1.49 (098) 2.49 (098) 2.49 (098) 2.40 (016)

D³PAK Package Outline

@3 100% Sn







Microsemi Headquarters

One Enterprise, Aliso Viejo, CA 92656 USA Within the USA: +1 (800) 713-4113 Outside the USA: +1 (949) 380-6100 Sales: +1 (949) 380-6136 Fax: +1 (949) 215-4996 Email: sales.support@microsemi.com

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